

LISTING OF CLAIMS

1. (Original) A method of fabricating a memory cell, comprising:  
forming a first conductive layer over a substrate;  
forming a superionic conductor over said first conductive layer;  
forming a polymer layer over said superionic conductor in a manner  
which produces a layer of mobile ions between said polymer layer and said superionic  
conductor; and  
forming a second conductive layer over said polymer layer.
2. (Original) The method of claim 1, wherein said superionic conductor is  
formed from a transition metal complex.
3. (Original) The method of claim 1, wherein said superionic conductor is  
selected from a group consisting of CuBr and Cu<sub>2</sub>Se.
4. (Original) The method of claim 1, wherein said polymer layer is formed  
from vinyl monomers.
- TP 5. (Original) The method of claim <sup>1</sup>~~5~~, wherein said vinyl monomers are  
selected from a group consisting of methacrylates, acrylates, styrenes, vinylpyridines,  
acrylonitrile, and acrylamides.
6. (Original) The method of claim 1, wherein forming the polymer layer  
comprises placing monomers in contact with said superionic conductive layer such that  
said superionic conductor acts as an initiator to form polymers from said monomers.